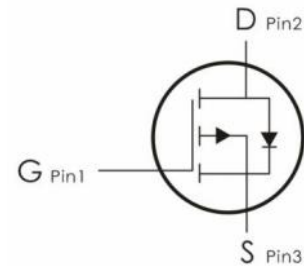
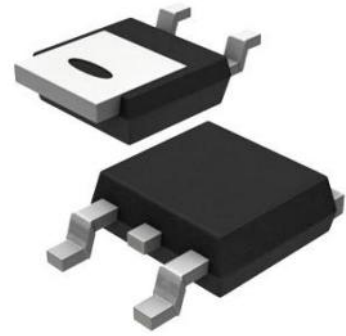


Description:

This P-Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge. It can be used in a wide variety of applications.

Features:

- 1) $V_{DS}=-30V, I_D=-40A, R_{DS(ON)}<14.5m\ \Omega @V_{GS}=-10V$
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra low $R_{DS(ON)}$.
- 5) Excellent package for good heat dissipation.



Package Marking and Ordering Information:

Part NO.	Marking	Package	Packing
DOD40P03	40P03	TO- 252	2500 pcs/Reel

Absolute Maximum Ratings: ($T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	± 25	V
I_D	Continuous Drain Current ³	-40	A
	Continuous Drain Current- $T_C=100^\circ\text{C}$ ³	-28	
I_{DM}	Pulsed Drain Current ⁴	-160	
P_D	Power Dissipation	39	W
E_{AS}	Single pulse avalanche energy ⁵	75	mJ
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55-+150	$^\circ\text{C}$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	3.2	$^\circ\text{C}/\text{W}$

R_{θJA}	Thermal Resistance, Junction to Ambient	56	°C/W
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Electrical Characteristics: (T_C=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250 μ A	-30	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	V _{GS} =0V, V _{DS} =-30V	---	---	-1	μ A
I_{GSS}	Gate-Source Leakage Current	V _{GS} =± 25V, V _{DS} =0A	---	---	± 100	nA
On Characteristics						
V_{GS(th)}	GATE-Source Threshold Voltage	V _{GS} =V _{DS} , I _D =250 μ A	-1.1	-1.5	-1.9	V
R_{DS(ON)}	Drain-Source On Resistance	V _{GS} =-10V, I _D =-10A	---	11	14.5	m Ω
		V _{GS} =-4.5V, I _D =-5A	---	15	19	m Ω
Dynamic Characteristics						
C_{iss}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz	---	1229	---	pF
C_{oss}	Output Capacitance					
C_{rss}	Reverse Transfer Capacitance					
Switching Characteristics						
t_{d(on)}	Turn-On Delay Time	V _{DS} =-15V, R _{ENG} =3 Ω, V _{GS} =-10V	---	17	---	ns
t_r	Rise Time		---	21	---	ns
t_{d(off)}	Turn-Off Delay Time		---	54	---	ns
t_f	Fall Time		---	41	---	ns
Q_g	Total Gate Charge	V _{GS} =-10V, V _{DS} =-15V,	---	26.3	---	nc
Q_{gs}	Gate-Source Charge		---	5	---	nc
Q_{gd}	Gate-Drain "Miller" Charge		---	4.2	---	nc
Drain-Source Diode Characteristics						
V_{SD}	Diode Forward Voltage ¹	V _{GS} =0V, I _{SD} =-1A	---	-0.75	-1	V
I_S	Continuous Drain Current ³	V _D =V _G =0V	---	---	-40	A
I_{SM}	Pulsed Drain Current		---	---	-160	A
T_{rr}	Reverse Recovery Time	I _F =-10A, T _J =25°C	---	32	---	ns

Qrr	Reverse Recovery Charge	di/dt=100A/us	---	28	---	nc
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Typical Characteristics: ($T_c=25^\circ\text{C}$ unless otherwise noted)

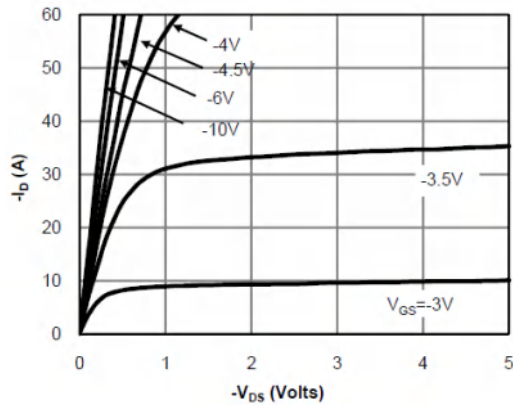


Figure 1. On-Regin Characteristics

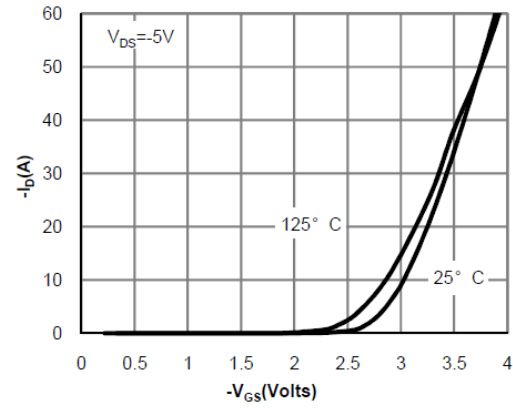


Figure 2 Transfer Characteristics

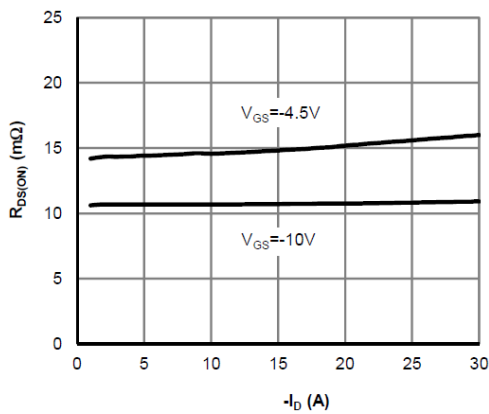


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

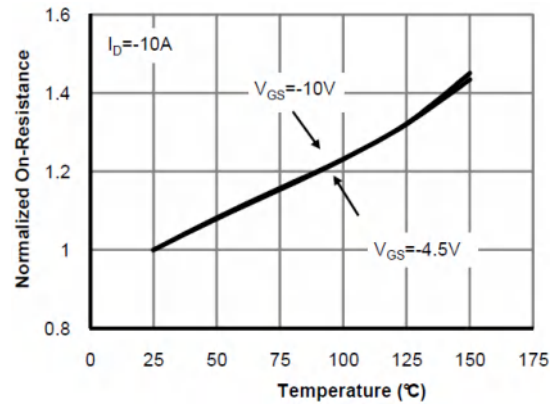


Figure 4. On-Resistance vs. Junction Temperature

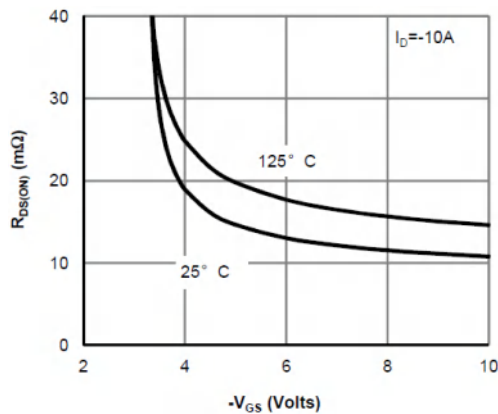


Figure 5. On-Resistance vs. Gate-Source Voltage

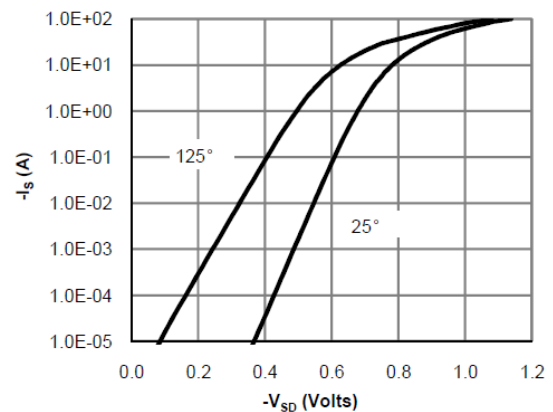


Figure 6 Body-Diode Characteristics

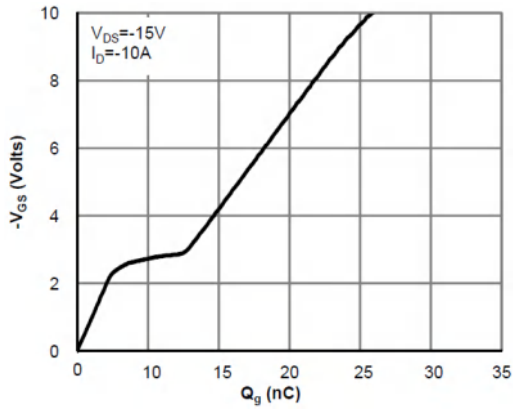


Figure 7 Gate-Charge Characteristics

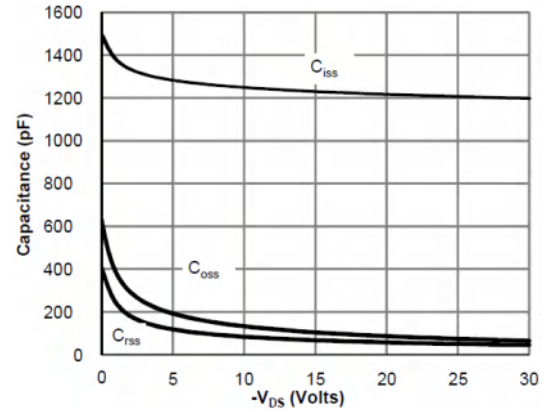


Figure 8 Capacitance Characteristics

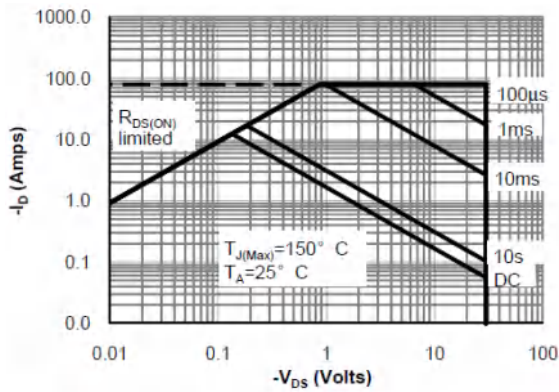


Figure 9 Maximum Forward Biased Safe Operating Area

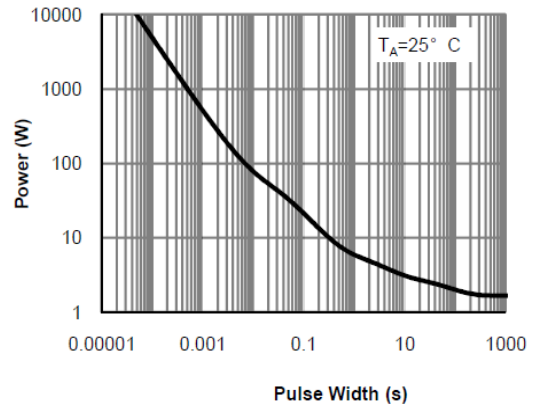


Figure 10 Single Pulse Power Rating Junction-

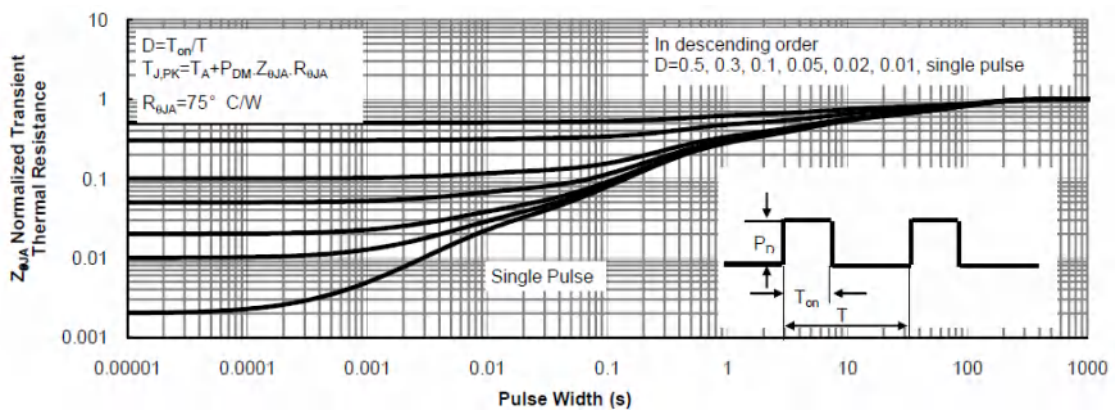
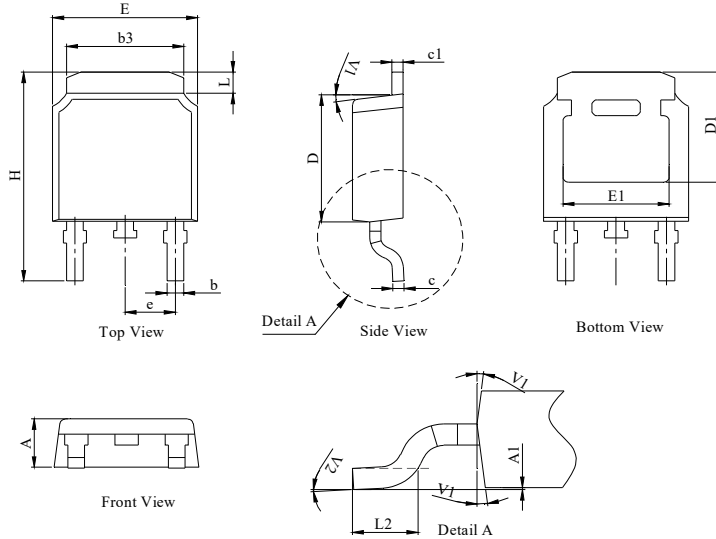


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-252 Package Information

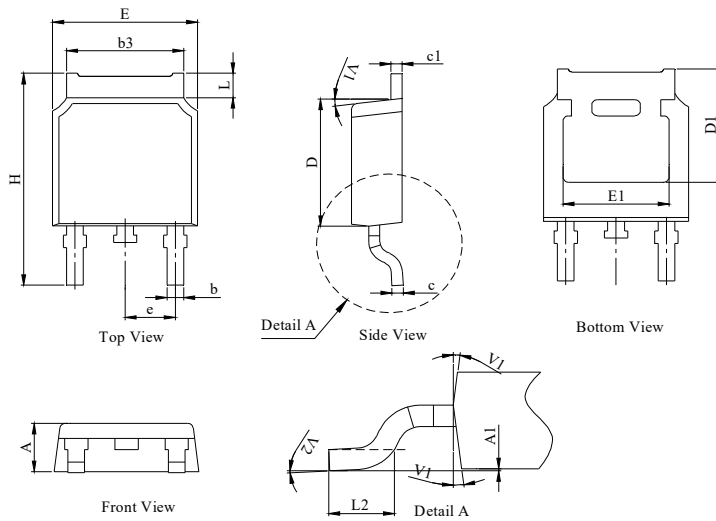
Package Outline Type-A

UNIT: mm



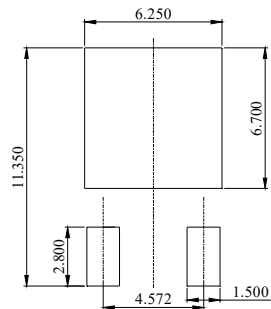
DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	2.18	2.30	2.39
A1	0	--	0.13
b	0.64	0.76	0.89
c	0.40	0.50	0.61
c1	0.46	0.50	0.58
D	5.97	6.10	6.23
D1	5.05	--	--
E	6.35	6.60	6.73
E1	4.32	--	--
b3	5.21	5.38	5.55
e	2.29 BSC		
H	9.40	10.00	10.40
L	0.89	--	1.27
L2	1.40	--	1.78
V1	7° REF		
V2	0°	--	6°

Package Outline Type-B



DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	2.10	2.30	2.40
A1	0	--	0.13
b	0.66	0.76	0.86
b3	5.21	5.38	5.55
c	0.40	0.50	0.60
c1	0.44	0.50	0.58
D	5.90	6.10	6.30
D1	5.30REF		
E	6.40	6.60	6.80
E1	4.63	-	-
e	2.29 BSC		
H	9.50	10.00	10.70
L	1.09	--	1.21
L2	1.35	--	1.65
V1	7° REF		
V2	0°	--	6°

Recommended Soldering Footprint



Marking Information:

①. Doingter LOGO

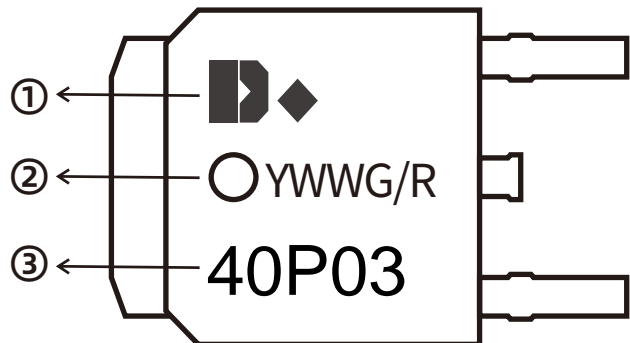
②. Date Code(YWWG / R)

Y : Year Code , last digit of the year


WW : Week Code(01-53)

G/R : G(Green) /R(Lead Free)

③. Part NO.



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